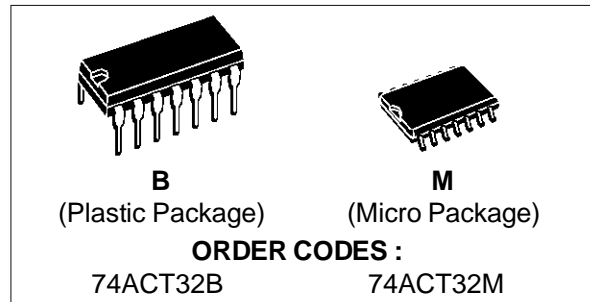# SGS-THOMSON MICROELECTRONICS

74ACT32

QUAD 2-INPUT OR GATE

- HIGH SPEED: t_{PD} = 4.5 ns (TYP.) at V_{CC} = 5V
- LOW POWER DISSIPATION:
  I_{CC} = 4 µA (MAX.) at T_A = 25 °C
- COMPATIBLE WITH TTL OUTPUTS
  V_{IH} = 2V (MIN), V_{IL} = 0.8V (MAX)
- 50Ω TRANSMISSION LINE DRIVING
  CAPABILITY
- SYMMETRICAL OUTPUT IMPEDANCE:
  $|I_{OH}|$ = I_{OL} = 24 mA (MIN)
- BALANCED PROPAGATION DELAYS:
  $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE:
  V_{CC} (OPR) = 4.5V to 5.5V
- PIN AND FUNCTION COMPATIBLE WITH
  74 SERIES 32
- IMPROVED LATCH-UP IMMUNITY

DESCRIPTION

The ACT32 is an advanced high-speed CMOS QUAD 2-INPUT OR GATE fabricated with sub-micron silicon gate and double-layer metal wiring C^2MOS technology. It is ideal for low power applications mantaining high speed

B
(Plastic Package)

M
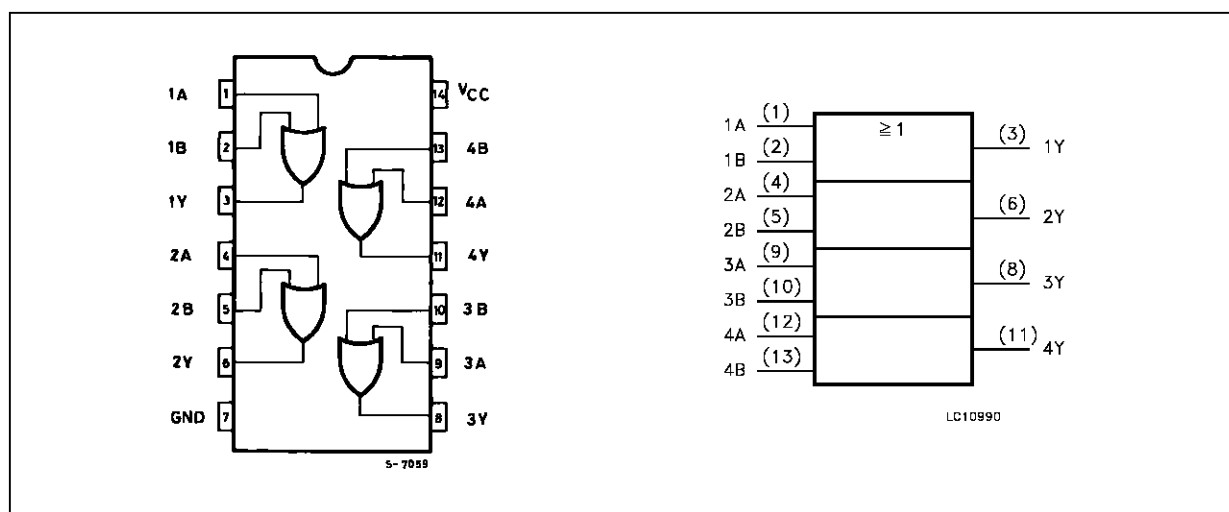(Micro Package)

ORDER CODES :

74ACT32B   74ACT32M

operation similar to equivalent Bipolar Schottky TTL.

The internal circuit is composed of 2 stages including buffer output, which enables high noise immunity and stable output.
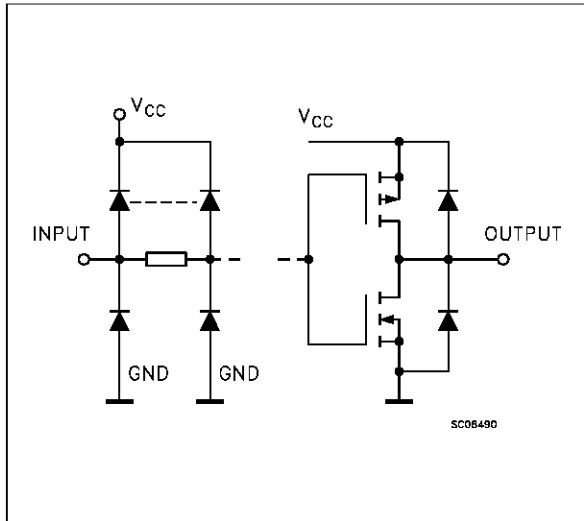
The device is designed to interface directly High Speed CMOS systems with TTL, NMOS and CMOS output voltage levels.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS

INPUT AND OUTPUT EQUIVALENT CIRCUIT

SC06490

PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 9, 12	1A to 4A	Data Inputs
2, 5, 10, 13	1B to 4B	Data Inputs
3, 6, 8, 11	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	V_{CC}	Positive Supply Voltage

TRUTH TABLE

A	B	Y
L	L	L
L	H	H
H	L	H
H	H	H

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 50	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 200	mA
T_{stg}	Storage Temperature	-65 to +150	^{o}C
T_L	Lead Temperature (10 sec)	300	^{o}C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	4.5 to 5.5	V
V_I	Input Voltage	0 to V_{CC}	V
V_O	Output Voltage	0 to V_{CC}	V
T_{op}	Operating Temperature:	-40 to +85	^{o}C
dt/dv	Input Rise and Fall Time V_{CC} = 4.5 to 5.5V (note 1)	8	ns/V

1) V_{IN} from 0.8 V to 2.0 V

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MICROELECTRONICS

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions		Value					Unit
		V_{CC} (V)		$T_A = 25\ ^oC$			-40 to 85 ^oC		
				Min.	Typ.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	4.5	$V_O = 0.1$ V or $V_{CC} - 0.1$ V	2.0	1.5		2.0		V
		5.5		2.0	1.5		2.0		
V_{IL}	Low Level Input Voltage	4.5	$V_O = 0.1$ V or $V_{CC} - 0.1$ V		1.5	0.8		0.8	V
		5.5			1.5	0.8		0.8	
V_{OH}	High Level Output Voltage	4.5	$V_I^{(*)} = V_{IH}$ or V_{IL} — $I_O = -50$ μA	4.4	4.49		4.4		V
		5.5	$I_O = -50$ μA	5.4	5.49		5.4		
		4.5	$I_O = -24$ mA	3.86			3.76		
		5.5	$I_O = -24$ mA	4.86			4.76		
V_{OL}	Low Level Output Voltage	4.5	$V_I^{(*)} = V_{IH}$ or V_{IL} — $I_O = 50$ μA		0.001	0.1		0.1	V
		5.5	$I_O = 50$ mA		0.001	0.1		0.1	
		4.5	$I_O = 24$ mA			0.36		0.44	
		5.5	$I_O = 24$ mA			0.36		0.44	
I_I	Input Leakage Current	5.5	$V_I = V_{CC}$ or GND			±0.1		±1	μA
I_{CCT}	Max I_{CC} /Input	5.5	$V_I = V_{CC} - 2.1$ V		0.6			1.5	mA
I_{CC}	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			4		40	μA
I_{OLD}	Dynamic Output Current (note 1, 2)	5.5	$V_{OLD} = 1.65$ V max					75	mA
I_{OHD}			$V_{OHD} = 3.85$ V min					-75	mA

1) Maximum test duration 2ms, one output loaded at time
2) Incident wave switching is guaranteed on transmission lines with impedances as low as 50 Ω.
(*) All outputs loaded.

AC ELECTRICAL CHARACTERISTICS ($C_L = 50$ pF, $R_L = 500$ Ω, Input $t_r = t_f = 3$ ns)

Symbol	Parameter	Test Condition		Value					Unit
		V_{CC} (V)		$T_A = 25\ ^oC$			-40 to 85 ^oC		
				Min.	Typ.	Max.	Min.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time	$5.0^{(*)}$			4.5	9.0		10.0	ns

(*) Voltage range is 5V ± 0.5V

CAPACITIVE CHARACTERISTICS

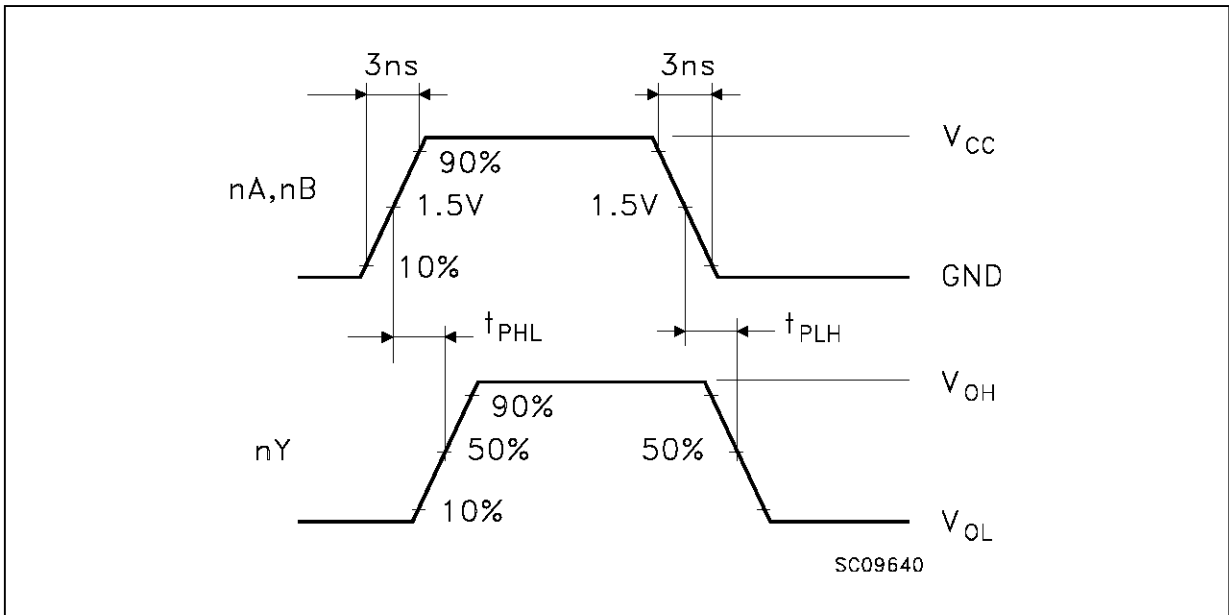| Symbol	Parameter	Test Conditions		Value					Unit
		V_{CC} (V)		$T_A = 25\ ^oC$			-40 to 85 ^oC		
				Min.	Typ.	Max.	Min.	Max.	
C_{IN}	Input Capacitance	5.0			4				pF
C_{PD}	Power Dissipation Capacitance (note 1)	5.0			30				pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/n$ (per circuit)
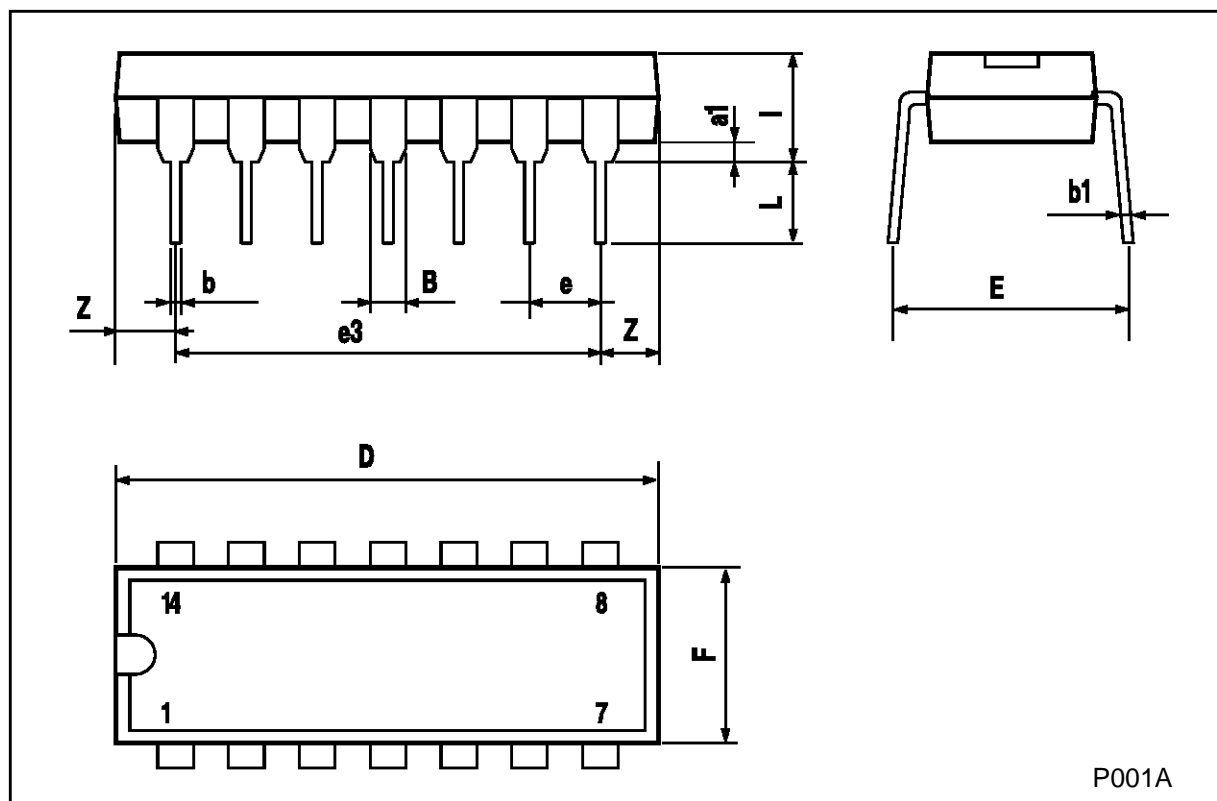
SGS-THOMSON MICROELECTRONICS

TEST CIRCUIT

$C_L = 50$ pF or equivalent (includes jig and probe capacitance)
$R_L = R_1 = 500\Omega$ or equivalent
$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)
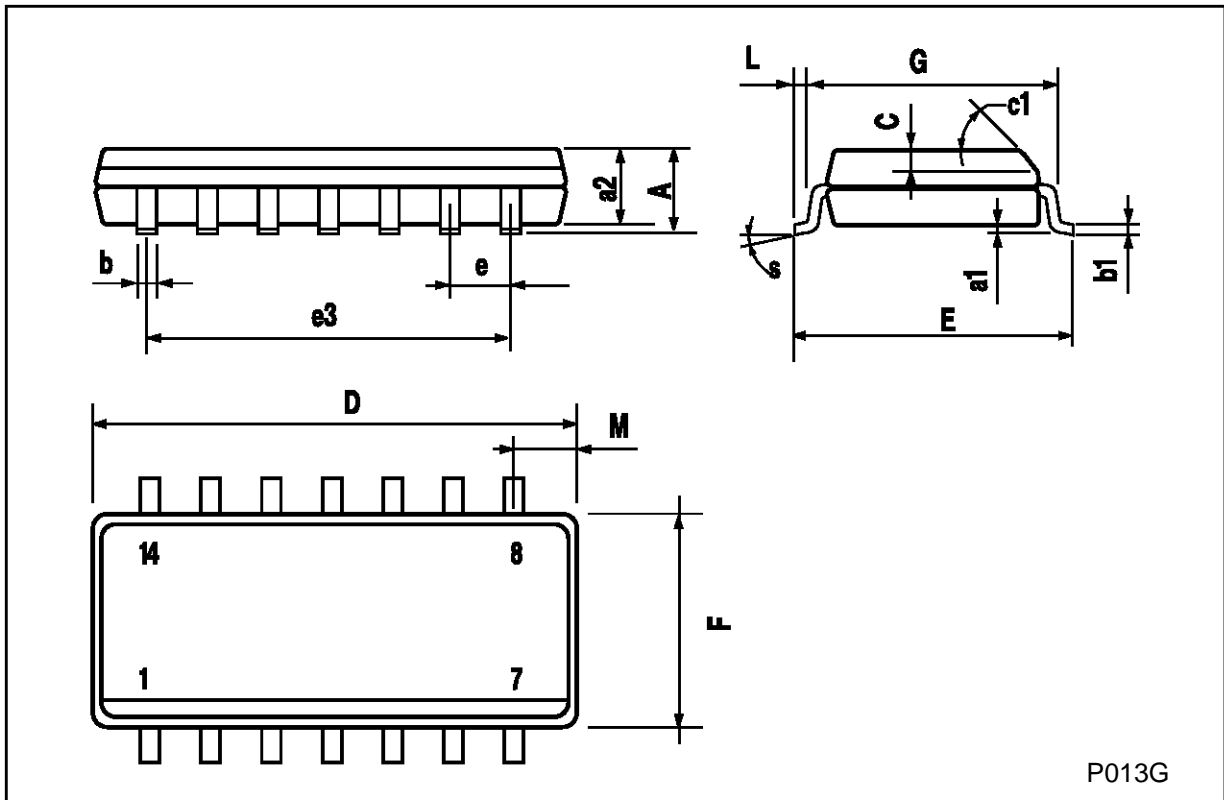
WAVEFORM: PROPAGATION DELAYS (f=1MHz; 50% duty cycle)

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Plastic DIP14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100

P001A

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SO14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45 (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8 (max.)					

P013G

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